

Contd  
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a fourth insulating film comprising silicon nitride formed on said third insulating film wherein said fourth insulating film substantially covers said semiconductor layer except for a contact hole,

wherein the first and fourth insulating films comprising silicon nitride are both formed over a portion of said substrate between the N-channel and P-channel type thin film transistors.

#### REMARKS

At the outset, the Examiner is thanked for the thorough review and consideration of the present application.

The Examiner's non-final Office Action dated September 7, 2000 has been received and its contents carefully noted. Claims 1-22 were pending in the present application. By this amendment, claim 15 has been amended. Accordingly, claims 1-22 are currently pending, of which 1, 4, 7, 10, 12, 15, 18, and 20 are independent.

Claims 1-2, 4-5, 7-8, 10-12, 14-15, 17-18, and 20-22 stand rejected under 35 U.S.C. § 102(b) as allegedly clearly anticipated by Wakai (U.S. Patent No. 5,424,230). Claims 3, 6, 9, 13, 16, and 19 stand rejected under 35 U.S.C. § 103(a) as allegedly unpatentable over Wakai. These rejections are respectfully traversed.

Applicants respectfully submit that the Wakai reference has a publication date of June 13, 1995, while the present application claims foreign priority based on foreign applications JP 4-102202, JP 4-113027, and JP 4-124324, which have the filing date of March 27, 1992, April 6, 1992, and April 17, 1992, respectively. Further, to perfect the foreign dates claimed, Applicants submit herewith a verified English translation for the JP 4-113027 and JP 4-124324 priority documents for consideration.

In view of the arguments set forth above, Applicants respectfully request the § 102(b) rejection of claims 1-2, 4-5, 7-8, 10-12, 14-15, 17-18, and 20-22 and the § 103 rejection of claims 3, 6, 9, 13, 16, and 19 be reconsidered and withdrawn.

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Art Unit: 2812

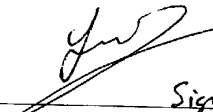
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CONCLUSION

Having responded to all rejections set forth in the outstanding non-final Office Action, it is submitted that claims 1-22 are now in condition for allowance. An early and favorable Notice of Allowance is respectfully solicited.

In the event that the Examiner is of the opinion that a brief telephone or personal interview will facilitate allowance of one or more of the above claims, the Examiner is courteously requested to contact Applicants' undersigned representative.

Respectfully submitted,

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Attachments: Version Of Amended Claims With Markings To Show Changes Made

**VERSION OF AMENDED CLAIMS WITH  
MARKINGS TO SHOW CHANGES MADE**

15. (Amended) A CMOS semiconductor device having an N-channel type thin film transistor and a P-channel type thin film transistor, each of which comprising:
- a first insulating film comprising silicon nitride formed on a substrate;
  - a second insulating film comprising silicon oxide formed on said first insulating film;
  - a semiconductor layer formed on said second insulating film wherein said semiconductor layer includes at least source, drain and channel regions;
  - a third insulating film comprising silicon oxide formed on said semiconductor layer;
  - a fourth insulating film comprising silicon nitride formed on said third insulating film wherein said fourth insulating film substantially covers said semiconductor layer except for a contact hole,
- wherein the first and fourth insulating films comprising silicon nitride are both formed over a portion of said substrate between [said first and second thin film transistors] the N-channel and P-channel type thin film transistors.